



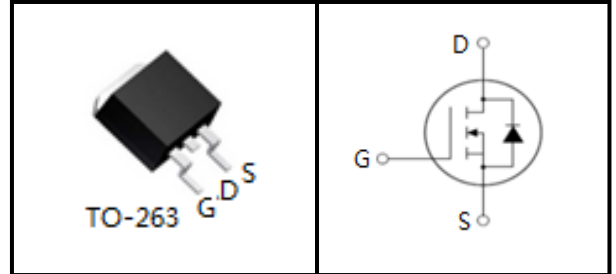
## 60V N-Channel DTMOS

### FEATURES

- Trench Power DTMOS Technology
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching Applications

### APPLICATIONS

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial



Device Marking and Package Information		
Device	Package	Marking
TSB15N06A	TO-263	15N06A

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	60	V
Continuous Drain Current (Package Limited)	$I_D$	180	A
Pulsed Drain Current (note1)	$I_{DM}$	720	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	609	mJ
Avalanche Current (note1)	$I_{AS}$	28	A
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	208	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.6	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	60	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 60V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	--	4	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$	--	2.5	3	m $\Omega$
Forward Transconductance (Note3)	$g_{fs}$	$V_{DS} = 10V, I_D = 50A$	--	140	--	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0\text{MHz}$	--	7710	--	pF
Output Capacitance	$C_{oss}$		--	667	--	
Reverse Transfer Capacitance	$C_{rss}$		--	66	--	
Total Gate Charge	$Q_g$	$V_{DD} = 30V, I_D = 50A,$ $V_{GS} = 10V$	--	138	--	nC
Gate-Source Charge	$Q_{gs}$		--	37	--	
Gate-Drain Charge	$Q_{gd}$		--	35.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 50A,$ $R_G = 25\Omega$	--	35	--	ns
Turn-on Rise Time	$t_r$		--	22	--	
Turn-off Delay Time	$t_{d(off)}$		--	105	--	
Turn-off Fall Time	$t_f$		--	45	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	50	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	150	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 50A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 50A,$ $di_F/dt = 500A/\mu s$	--	50	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	110	--	nC

**Notes**

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{AS} = 28A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width  $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

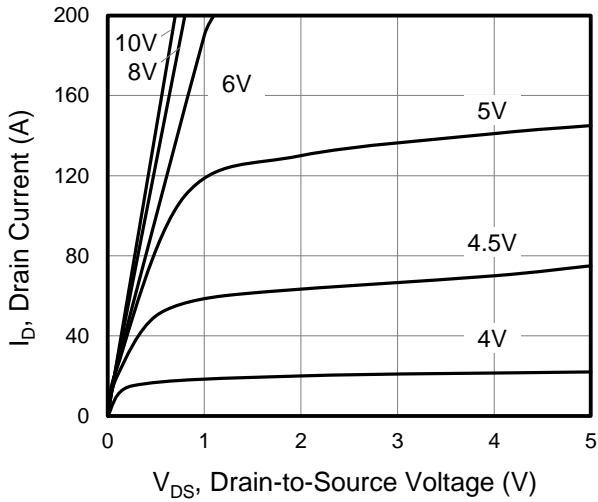


Figure 2. Transfer Characteristics

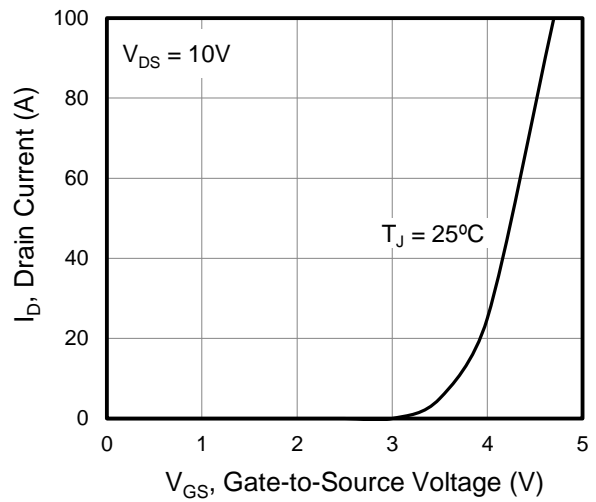


Figure 3. On-Resistance vs. Drain Current

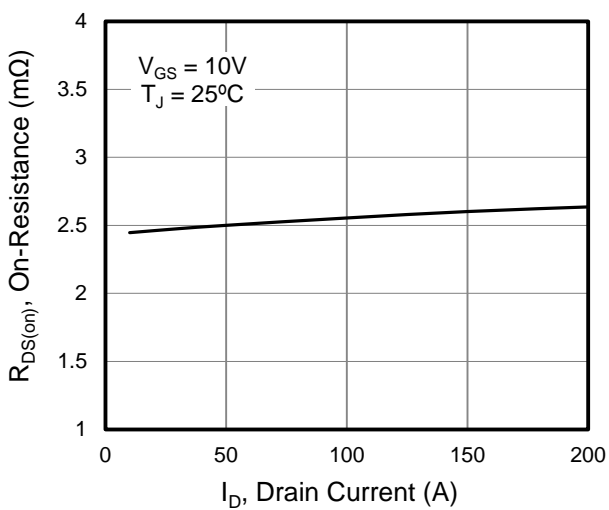


Figure 4. Capacitance

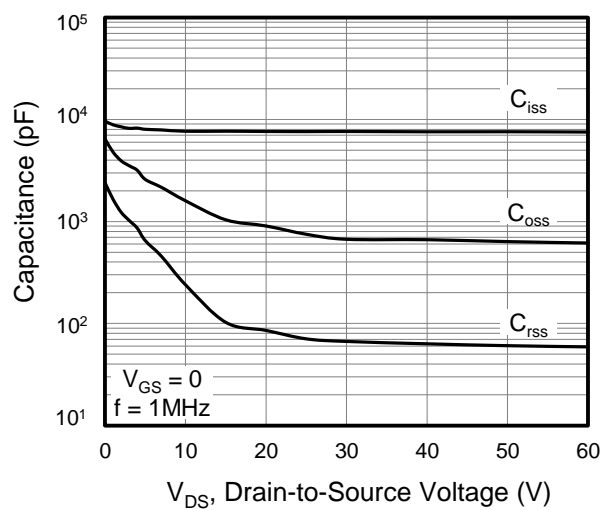


Figure 5. Gate Charge

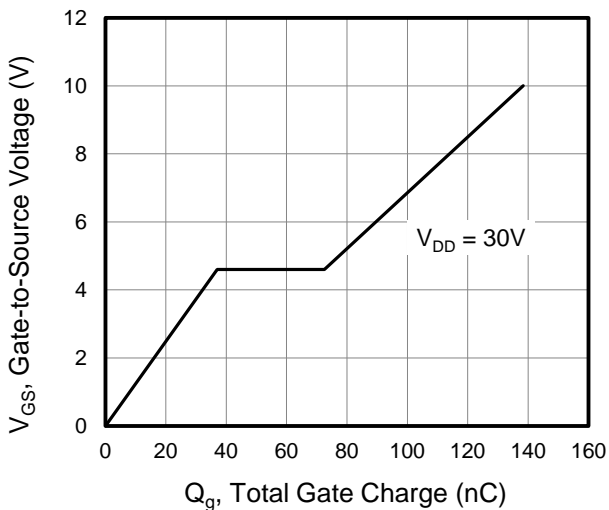
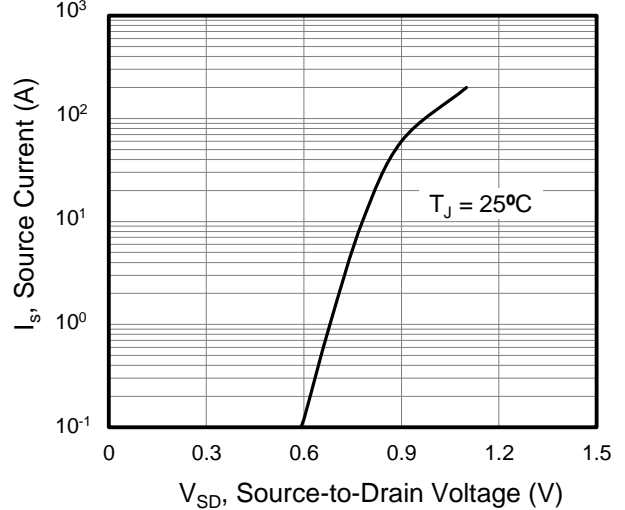


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

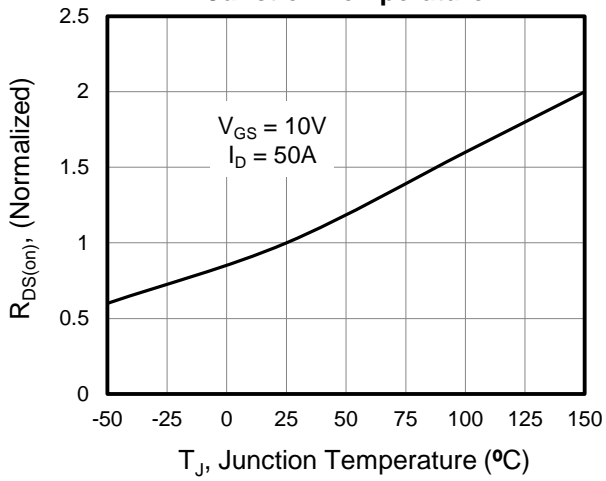


Figure 8. Threshold Voltage vs. Junction Temperature

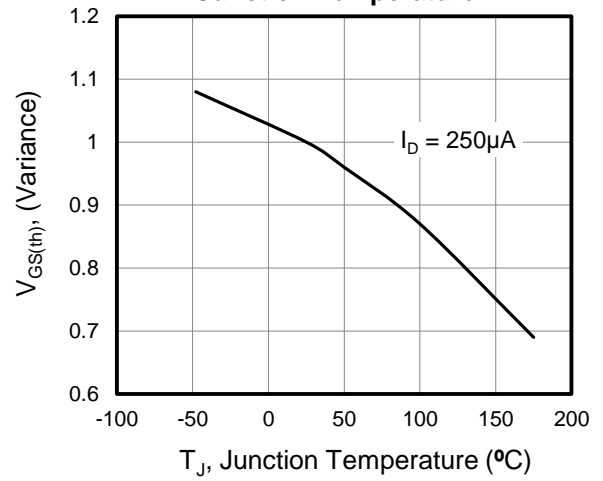


Figure 9. Transient Thermal Impedance

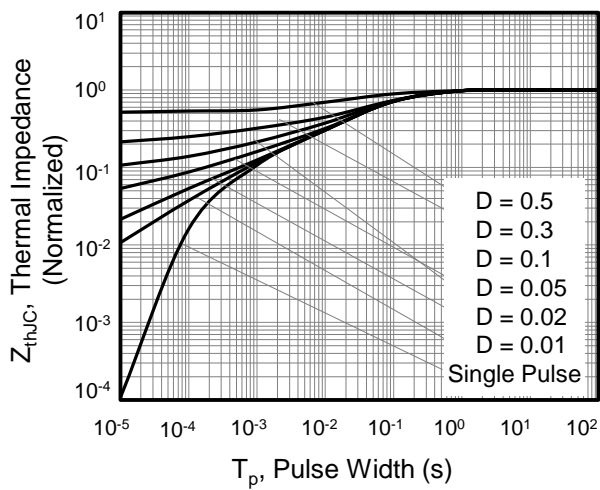




Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

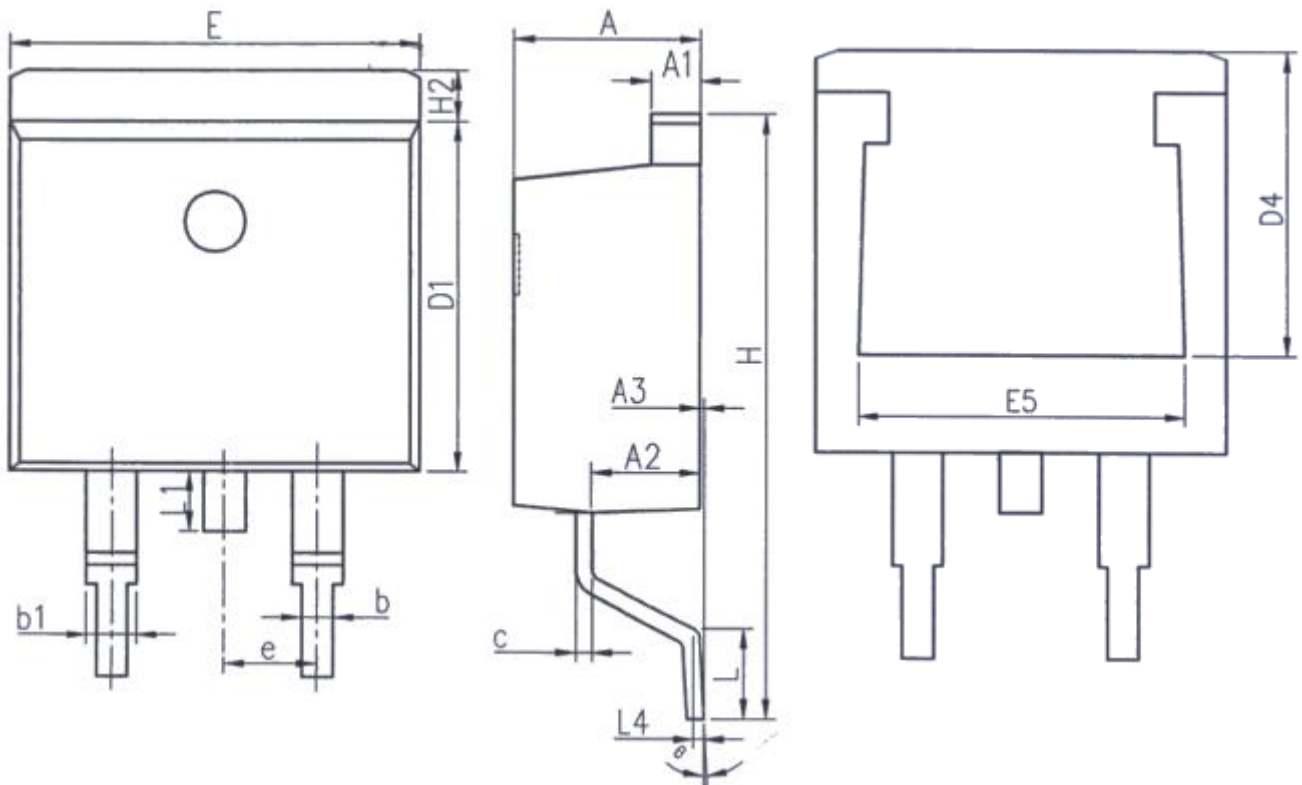


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





### TO-263



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.49	2.89
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.50	8.90
D4	6.60	-

Unit: mm		
Symbol	Min.	Max.
E	9.86	10.36
E5	7.06	-
e	2.54BSC	
H	14.70	15.50
H2	1.07	1.47
L	2.00	2.60
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°



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